

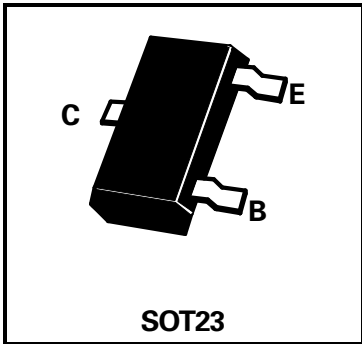
SOT23 NPN SILICON PLANAR HIGH VOLTAGE HIGH PERFORMANCE TRANSISTOR

ISSUE 3 – DECEMBER 1995 

FMMT497

COMPLIMENTARY TYPE – FMMT597

PARTMARKING DETAIL – 497



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CB0}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	500	mA
Peak Pulse Current	I_{CM}	1	A
Base Current	I_B	200	mA
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	300		V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{CEO(sus)}$	300		V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}		100	nA	$V_{CB}=250V$
Collector Cut-Off Current	I_{CES}		100	nA	$V_{CES}=250V$
Emitter Cut-Off Current	I_{EBO}		100	nA	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.2 0.3	V V	$I_C=100mA, I_B=10mA$ $I_C=250mA, I_B=25mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.0	V	$I_C=250mA, I_B=25mA$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		1.0	V	$I_C=250mA, V_{CE}=10V$
Static Forward Current Transfer Ratio	h_{FE}	100 80 20	300		$I_C=1mA, V_{CE}=10V$ $I_C=100mA, V_{CE}=10V^*$ $I_C=250mA, V_{CE}=10V^*$
Transition Frequency	f_T	75		MHz	$I_C=50mA, V_{CE}=10V$ $f=100MHz$
Collector-Base Breakdown Voltage	C_{obo}		5	pF	$V_{CB}=10V, f=1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle \leq 2%

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TYPICAL CHARACTERISTICS

